#### October 2006

# STTH2R02

## Ultrafast recovery diode

### Main product characteristics

I <sub>F(AV)</sub>	2 A
V <sub>RRM</sub>	200 V
T <sub>j</sub> (max)	175° C
V <sub>F</sub> (typ)	0.7 V
t <sub>rr</sub> (typ)	15 ns

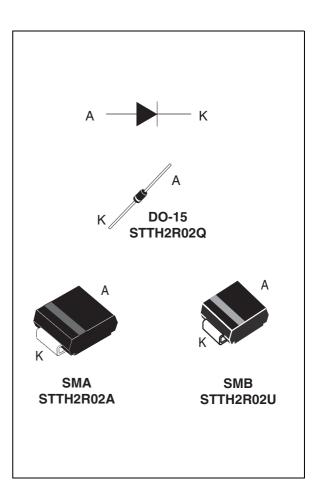
### Features and benefits

- Very low conduction losses
- Negligible switching losses
- Low forward and reverse recovery times
- High junction temperature

### Description

The STTH2R02 uses ST's new 200 V planar Pt doping technology, and it is specially suited for switching mode base drive and transistor circuits.

Packaged in DO-15, SMA, and SMB, this device is intended for use in low voltage, high frequency inverters, free wheeling and polarity protection.



### Order codes

Part Number	Marking
STTH2R02Q	STTH2R02
STTH2R02QRL	STTH2R02
STTH2R02A	R2A
STTH2R02U	R2U

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# 1 Characteristics

#### Table 1. Absolute ratings (limiting values at $T_i = 25^\circ$ C, unless otherwise specified)

Symbol	Parameter			Value	Unit
V <sub>RRM</sub>	Repetitive peak reverse voltage			200	V
1	I <sub>FBM</sub> Repetitive peak forward current	DO-15 <sup>(1)</sup>	$t_p = 5 \ \mu s, F = 5 \ kHz$	60	А
<sup>I</sup> FRM		SMA, SMB		60	A
DMS forward ourrant	DO-15		60	А	
<sup>I</sup> F(RMS)	I <sub>F(RMS)</sub> RMS forward current	SMA, SMB		00	A
1	Average forward current, $\delta = 0.5$	DO-15	$T_{lead} = 90^{\circ} C$	2	А
'F(AV)	$I_{F(AV)}$ Average forward current, $\delta = 0.5$		$T_c = 90^\circ C$	Z	7
I <sub>FSM</sub>	Surge non repetitive forward current $t_p = 10 \text{ ms Sinusoidal}$			75	А
T <sub>stg</sub>	Storage temperature range				° C
Тj	Maximum operating junction temperature	175	°C		

1. On infinite heatsink with 10 mm lead length

#### Table 2.Thermal parameters

Symbol	Parameter			Value	Unit
D	Junction to lead Lead Length = 10 mm on infinite heatsink DO			45	° C/W
R <sub>th(j-c)</sub>	Junction to case		SMA, SMB	30	0/11

#### Table 3. Static electrical characteristics

Symbol	Parameter	Test conditions		Min.	Тур	Max.	Unit
I <sub>B</sub> <sup>(1)</sup>	Povorco logkago ourront	T <sub>j</sub> = 25° C	V - V			3	
I <sub>R</sub> <sup>(1)</sup> Reverse leakage current	neverse leakage current	T <sub>j</sub> = 125° C	$V_{R} = V_{RRM}$		2	20	μA
	$T_{j} = 25^{\circ} C \qquad I_{F} = 6 A$ $T_{j} = 25^{\circ} C \qquad I_{F} = 6 A$	I <sub>F</sub> = 6 A			1.20		
V <sub>F</sub> <sup>(2)</sup>		$T_j = 25^\circ C$			0.89	1.0	v
V <sub>F</sub> <sup>(2)</sup> Forward voltage drop	$T_j = 100^\circ C$	I <sub>F</sub> = 2 A		0.76	0.85	v	
		T <sub>j</sub> = 150° C			0.70	0.80	

1. Pulse test:  $t_p = 5 \text{ ms}, \delta < 2 \%$ 

2. Pulse test: tp = 380  $\mu$ s,  $\delta$  < 2 %

To evaluate the conduction losses use the following equation: P = 0.68 x  $I_{F(AV)}$  + 0.06  ${I_F}^2_{(RMS)}$ 



Table 4.Dynamic characteristics

Symbol	Parameter	Test conditions	Min.	Тур	Max.	Unit
		$\label{eq:IF} \begin{array}{l} I_{F} = 1 \ A, \ dI_{F}/dt = \text{-50 } A/\mus, \\ V_{R} = 30 \ V, \ T_{j} = 25^{\circ} \ C \end{array}$		23	30	ns
t <sub>rr</sub> Reverse recovery time	$\label{eq:IF} \begin{array}{l} I_F = 1 \mbox{ A, } dI_F/dt = -100 \mbox{ A/}\mu s, \\ V_R = 30 \mbox{ V, } T_j = 25^\circ \mbox{ C} \end{array}$		15	20	115	
I <sub>RM</sub>	Reverse recovery current	$    I_F = 2 \text{ A}, \text{ d}I_F/\text{d}t = -200 \text{ A}/\mu\text{s}, \\ V_R = 160 \text{ V}, T_j = 125^\circ \text{ C} $		3	4	А
t <sub>fr</sub>	Forward recovery time	$I_F$ = 2 A, dI <sub>F</sub> /dt = 100 A/µs V <sub>FR</sub> = 1.1 x V <sub>Fmax</sub> , T <sub>j</sub> = 25° C		40		ns
$V_{FP}$	Forward recovery voltage	$I_F = 2 \text{ A}, \text{ d}I_F/\text{d}t = 100 \text{ A}/\mu\text{s},$ $T_j = 25^{\circ} \text{ C}$		2.0		V



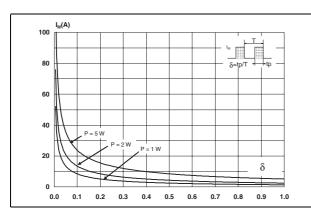


Figure 3. Forward voltage drop versus forward current (maximum values)

Figure 2. Forward voltage drop versus forward current (typical values)

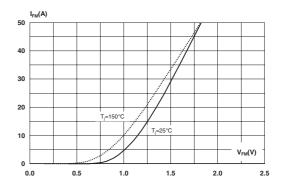
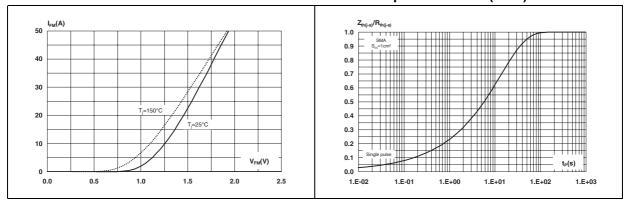


Figure 4. Relative variation of thermal impedance junction to case versus pulse duration (SMA)



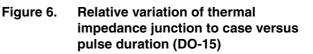
t<sub>⊳</sub>(s)

1.E+02

.tt

1.E+03

# Figure 5. Relative variation of thermal impedance junction to case versus pulse duration (SMB)



Z<sub>th(j-a)</sub>/R<sub>th(j-a</sub>

DO-15

1.0

0.9

0.8

0.7

0.6

0.5

0.4

0.3

0.2

0.1

0.0

1.E-03

1.E-02

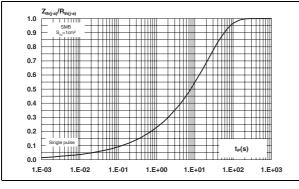
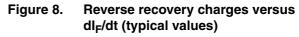


Figure 7. Junction capacitance versus reverse applied voltage (typical values)



1.E+00

1.E+01

1.E-01

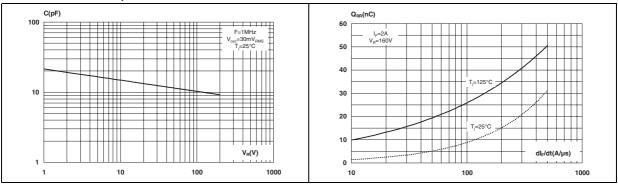
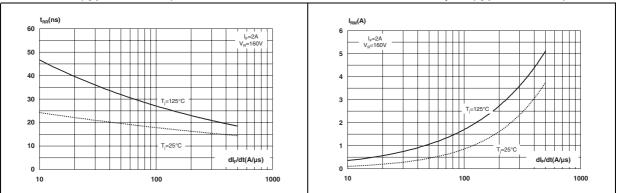


Figure 9.Reverse recovery time versus dl<sub>F</sub>/dt Figure 10.Peak reverse recovery current<br/>versus dl<sub>F</sub>/dt (typical values)

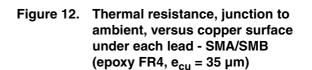


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S<sub>CU</sub>(cm<sup>2</sup>)

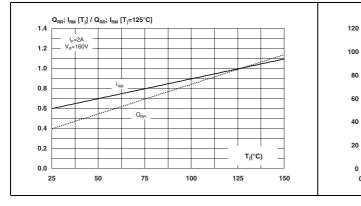
5.0

# Figure 11. Dynamic parameters versus junction temperature

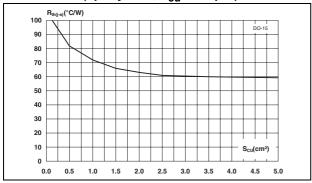


R<sub>th(i-a)</sub>(°C/W)

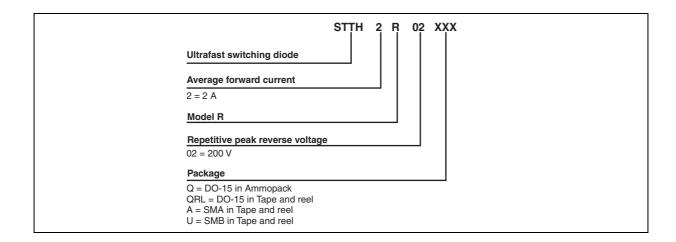
0.0 0.5 1.0 1.5 2.0 2.5 3.0 3.5 4.0 4.5



#### Figure 13. Thermal resistance, junction to ambient, versus copper surface under each lead DO-15 (epoxy FR4, $e_{cu} = 35 \mu m$ )



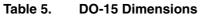
# 2 Ordering information scheme

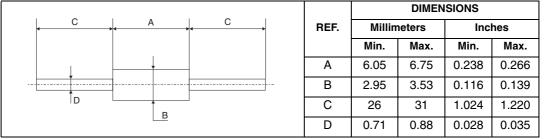


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# **3** Package information

Epoxy meets UL94, V0







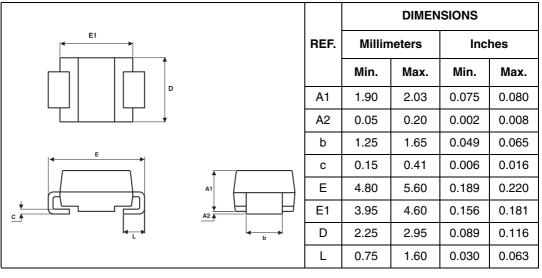


Figure 14. SMA footprint (dimensions in mm)

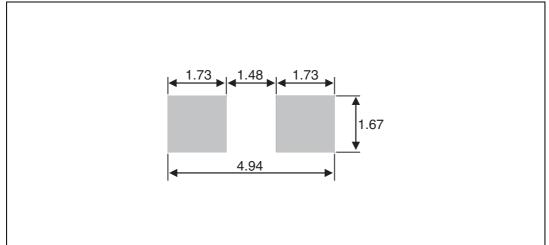
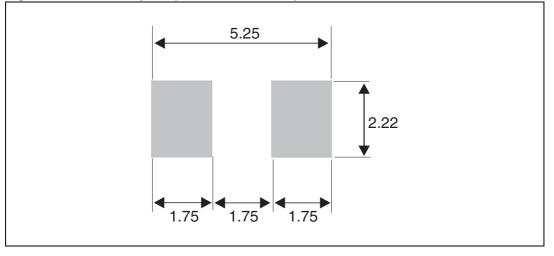




Table 7. SWD dimensions							
				DIMEN	ISIONS		
E1 →		Millimeters			Inches		
		Min.		Max.	Min.		Max.
	A1	1.90	2.15	2.45	0.075	0.085	0.096
	A2	0.05	0.15	0.20	0.002	0.006	0.008
	b	1.95		2.20	0.077		0.087
E►	с	0.15		0.41	0.006		0.016
	Е	5.10	5.40	5.60	0.201	0.213	0.220
	E1	4.05	4.30	4.60	0.159	0.169	0.181
		3.30	3.60	3.95	0.130	0.142	0.156
L	L	0.75	1.15	1.60	0.030	0.045	0.063

Table 7.SMB dimensions

Figure 15. SMB footprint (dimensions in mm)



In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com.

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# 4 Ordering information

Part Number	Marking	Package	Weight	Base qty	Delivery mode
STTH2R02Q	STTH2R02	DO-15	0.4 g	1000	Ammopack
STTH2R02QRL	STTH2R02	DO-15	0.4 g	6000	Tape and reel
STTH2R02A	R2A	SMA	0.068 g	5000	Tape and reel
STTH2R02U	R2U	SMB	0.12 g	2500	Tape and reel

# 5 Revision history

Date	Revision	Description of Changes
03-May-2006	1	First issue
13-Oct-2006	2	Maximum $T_j$ set to 175° C for all packages in Table 1.



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